

IN THE CLAIMS:

1. (Currently Amended) A semiconductor device, comprising:
a bulk substrate;
a multiple thickness buried oxide layer formed above said bulk substrate, said multiple thickness buried oxide layer having a substantially planar upper surface; and
an active layer formed above said multiple thickness buried oxide layer, said semiconductor device being formed in said active layer above said multiple thickness buried oxide layer.
2. (Original) The device of claim 1, wherein said bulk substrate is comprised of silicon.
3. (Original) The device of claim 1, wherein said semiconductor device is a transistor.
4. (Original) The device of claim 1, wherein said semiconductor device is part of at least one of a microprocessor, a memory device and a logic device.
5. (Original) The device of claim 1, wherein said active layer is comprised of silicon.

6. (Original) The device of claim 1, wherein said active layer has a thickness ranging from approximately 5-30 nm.

7. (Original) The device of claim 1, wherein said buried oxide layer is comprised of silicon dioxide.

8. (Original) The device of claim 1, wherein said multiple thickness buried oxide layer comprises:

a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections.

9. (Original) The device of claim 1, wherein said semiconductor device is a transistor having a channel region, at least a portion of said channel region being positioned above a section of said buried oxide layer that has a thickness that is less than a thickness of a remaining portion of said buried oxide layer.

10. (Original) The device of claim 1, wherein said semiconductor device is a transistor comprised of a gate electrode and wherein said multiple thickness buried oxide layer has a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than a thickness of said second sections, said first section being at least partially positioned under said gate electrode.

11. (Original) The device of claim 1, wherein said semiconductor device is a transistor comprised of a gate electrode and wherein said multiple thickness buried oxide layer has a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than a thickness of said second sections, said first section being substantially aligned with said gate electrode.

12. (Original) The device of claim 8, wherein said first section has a thickness ranging from approximately 30-50 nm and said second sections have a thickness ranging from approximately 120-180 nm.

13. (Currently Amended) A transistor, comprising:
a bulk substrate;
a buried oxide layer formed above said bulk substrate, said buried oxide layer comprising
a substantially planar upper surface, a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections; and
an active layer formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer.

14. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said bulk substrate is comprised of silicon.

15. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said transistor is part of at least one of a microprocessor, a memory device and a logic device.

16. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said active layer is comprised of silicon.

17. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said active layer has a thickness ranging from approximately 5-30 nm.

18. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said buried oxide layer is comprised of silicon dioxide.

19. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said transistor comprises a channel region, at least a portion of said channel region being positioned above at least a portion of said first section of said buried oxide layer.

20. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said transistor comprises a gate electrode and wherein said first section of said buried oxide layer is at least partially positioned under said gate electrode.

21. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said transistor comprises a gate electrode and wherein said first section of said buried oxide layer is substantially aligned with said gate electrode.

22. (Currently Amended) The ~~device~~ transistor of claim 13, wherein said first section has a thickness ranging from approximately 30-50 nm and said second sections have a thickness ranging from approximately 120-180 nm.

23. (Currently Amended) A transistor comprised of a channel region, said transistor comprising:

a bulk silicon substrate;

a buried oxide layer formed above said bulk silicon substrate, said buried oxide layer comprising a substantially planar upper surface, a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections; and

an active layer formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer, at least a portion of said channel region being positioned above said first section of said buried oxide layer.

24. (Currently Amended) The ~~device~~ transistor of claim 23, wherein said transistor is part of at least one of a microprocessor, a memory device and a logic device.

25. (Currently Amended) The ~~device~~ transistor of claim 23, wherein said active layer is comprised of silicon.

26. (Currently Amended) The ~~device~~ transistor of claim 23, wherein said active layer has a thickness ranging from approximately 5-30 nm.

27. (Currently Amended) The ~~device~~ transistor of claim 23, wherein said buried oxide layer is comprised of silicon dioxide.

28. (Currently Amended) The ~~device~~ transistor of claim 23, wherein said transistor further comprises a gate electrode and wherein said first section of said buried oxide layer is at least partially positioned under said gate electrode.

29. (Currently Amended) The ~~device~~ transistor of claim 23, wherein said transistor further comprises a gate electrode and wherein said first section of said buried gate oxide layer is substantially aligned said gate electrode.

30. (Currently Amended) The ~~device~~ transistor of claim 23, wherein said first section has a thickness ranging from approximately 30-50 nm and said second sections have a thickness ranging from approximately 120-180 nm.

31.-48. (Canceled)

49. (New) A semiconductor device, comprising:

a bulk substrate;

a multiple thickness buried oxide layer formed above said bulk substrate; and

an active layer formed above said multiple thickness buried oxide layer, said active layer

having a substantially planar lower surface, said semiconductor device being formed in said active layer above said multiple thickness buried oxide layer.

50. (New) The device of claim 49, wherein said semiconductor device is a transistor.

51. (New) The device of claim 49, wherein said semiconductor device is part of at least one of a microprocessor, a memory device and a logic device.

52. (New) A transistor, comprising:

a bulk substrate;

a buried oxide layer formed above said bulk substrate, said buried oxide layer comprising

a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections; and

an active layer formed above said buried oxide layer, said active layer having a substantially planar lower surface, said transistor being formed in said active layer above said buried oxide layer.

53. (New) The transistor of claim 52, wherein said transistor comprises a gate electrode and wherein said first section of said buried oxide layer is at least partially positioned under said gate electrode.

54. (New) The transistor of claim 52, wherein said transistor comprises a gate electrode and wherein said first section of said buried oxide layer is substantially aligned with said gate electrode.

55. (New) A transistor, comprising:

a bulk substrate;

a buried oxide layer formed above said bulk substrate, said buried oxide layer comprising

a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections, said first section being substantially aligned with a gate electrode of said transistor; and

an active layer formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer.

56. (New) A semiconductor device, comprising:

a bulk substrate;

a multiple thickness buried oxide layer formed above said bulk substrate;

an active layer formed above said multiple thickness buried oxide layer, said semiconductor device being formed in said active layer above said multiple thickness buried oxide layer; and

a doped back gate region positioned at least partially in said bulk substrate under said multiple thickness buried oxide layer.

57. (New) The device of claim 56, wherein said multiple thickness buried oxide layer comprises:

a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections.

58. (New) A transistor, comprising:

a bulk substrate;

a buried oxide layer formed above said bulk substrate, said buried oxide layer comprising

a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections;

an active layer formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer; and

a doped back gate region positioned at least partially in said bulk substrate under said buried oxide layer

59. (New) The transistor of claim 58, wherein said transistor comprises a gate electrode and wherein said first section of said buried oxide layer is substantially aligned with said gate electrode.

60. (New) A transistor comprised of a channel region, said transistor comprising:
a bulk silicon substrate;
a buried oxide layer formed above said bulk silicon substrate, said buried oxide layer comprising a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections;
an active layer formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer, at least a portion of said channel region being positioned above said first section of said buried oxide layer; and
a doped back gate region positioned at least partially in said bulk substrate under said buried oxide layer

61. (New) The transistor of claim 60, wherein said transistor further comprises a gate electrode and wherein said first section of said buried gate oxide layer is substantially aligned with said gate electrode.

62. (New) The device of claim 1, further comprising a doped back gate region positioned at least partially on said bulk substrate under said multiple thickness buried oxide layer.

63. (New) The transistor of claim 13, further comprising a doped back gate region positioned at least partially on said bulk substrate under said buried oxide layer.

64. (New) The transistor of claim 23, further comprising a doped back gate region positioned at least partially on said bulk substrate under said buried oxide layer.

65. (New) The transistor of claim 49, further comprising a doped back gate region positioned at least partially on said bulk substrate under said multiple thickness buried oxide layer.

66. (New) The transistor of claim 52, further comprising a doped back gate region positioned at least partially on said bulk substrate under said buried oxide layer.

67. (New) A semiconductor device, comprising:

a bulk substrate;

a multiple thickness buried oxide layer formed above said bulk substrate; and

an active layer having a thickness ranging from approximately 5-30 nm formed above

said multiple thickness buried oxide layer, said semiconductor device being

formed in said active layer above said multiple thickness buried oxide layer.

68. (New) A transistor, comprising:

a bulk substrate;

a buried oxide layer formed above said bulk substrate, said buried oxide layer comprising

a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections; and

an active layer having a thickness ranging from approximately 5-30 nm formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer.

69. (New) The transistor of claim 68, wherein said transistor comprises a gate electrode and wherein said first section of said buried oxide layer is substantially aligned with said gate electrode.

70. (New) A transistor, comprising:

a bulk substrate;

a buried oxide layer formed above said bulk substrate, said buried oxide layer comprising

a first section positioned between two second sections, said first section having a thickness ranging from approximately 30-50 nm and each of said second sections having a thickness ranging from approximately 120-180 nm, said thickness of said first section being less than said thickness of said second sections; and

an active layer formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer.

71. (New) The transistor of claim 70, wherein said transistor comprises a gate electrode and wherein said first section of said buried oxide layer is substantially aligned with said gate electrode.

72. (New) A transistor comprised of a channel region, said transistor comprising:
a bulk silicon substrate;
a buried oxide layer formed above said bulk silicon substrate, said buried oxide layer comprising a first section positioned between two second sections, said first section having a thickness and each of said second sections having a thickness, said thickness of said first section being less than said thickness of said second sections; and
an active layer having a thickness ranging from approximately 5-30 nm formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer, at least a portion of said channel region being positioned above said first section of said buried oxide layer.

73. (New) A transistor comprised of a channel region, said transistor comprising:
a bulk silicon substrate;
a buried oxide layer formed above said bulk silicon substrate, said buried oxide layer comprising a first section positioned between two second sections, said first

section having a thickness ranging from approximately 30-50 nm and each of said second sections having a thickness ranging from approximately 120-180 nm, said thickness of said first section being less than said thickness of said second sections; and

an active layer formed above said buried oxide layer, said transistor being formed in said active layer above said buried oxide layer, at least a portion of said channel region being positioned above said first section of said buried oxide layer.